

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	56	(gate adj oxide) and nitride and polysilicon and barrier and interface and combination and thermal and RTP and ion and implant\$	USPAT	OR	ON	2005/02/28 13:10
L2	13	(gate adj oxide) and nitride and polysilicon and barrier and interface and combination and thermal and RTP and ion and implant\$ and (nitrogen adj ion)	USPAT	OR	ON	2005/02/28 13:10
L3	13	2 and (kev or 1e16 or atoms or gas or source or nitrogen or dose or concentration or energy or barrier or substrate or interface or sequential or sequentially or treatment or process or thermal or ambient or ramp or temperature or "100" or "900" or "1100" or gate or oxide or nitride or polysilicon)	USPAT	OR	ON	2005/02/28 13:23
L4	13	2 and (kev or 1e16 or atoms or gas or source or nitrogen or dose or concentration or energy or barrier or substrate or interface or sequential or sequentially or treatment or process or thermal or ambient or ramp or temperature or "100" or "900" or "1100" or gate or oxide or nitride or polysilicon or RTP or rapid)	USPAT	OR	ON	2005/02/28 14:11
L5	1	("6287987").PN.	USPAT	OR	OFF	2005/02/28 14:07
L6	1	5 and (kev or 1e16 or atoms or gas or source or nitrogen or dose or concentration or energy or barrier or substrate or interface or sequential or sequentially or treatment or process or thermal or ambient or ramp or temperature or "100" or "900" or "1100" or gate or oxide or nitride or polysilicon or RTP or rapid)	USPAT	OR	ON	2005/02/28 14:09
L7	1	("6562730").PN.	USPAT	OR	OFF	2005/02/28 14:07

L8	1	7 and (kev or 1e16 or atoms or gas or source or nitrogen or dose or concentration or energy or barrier or substrate or interface or sequential or sequentially or treatment or process or thermal or ambient or ramp or temperature or "100" or "900" or "1100" or gate or oxide or nitride or polysilicon or RTP or rapid)	USPAT	OR	ON	2005/02/28 14:07
L9	1	("6450116").PN.	USPAT	OR	OFF	2005/02/28 14:09
L10	1	9 and (kev or 1e16 or atoms or gas or source or nitrogen or dose or concentration or energy or barrier or substrate or interface or sequential or sequentially or treatment or process or thermal or ambient or ramp or temperature or "100" or "900" or "1100" or gate or oxide or nitride or polysilicon or RTP or rapid)	USPAT	OR	ON	2005/02/28 14:09
L11	398	438/663	USPAT	OR	ON	2005/02/28 14:12
L12	1506	438/643	USPAT	OR	ON	2005/02/28 14:12
L13	1644	438/653	USPAT	OR	ON	2005/02/28 14:12
L14	467	438/659	USPAT	OR	ON	2005/02/28 14:12
L15	123	438/590	USPAT	OR	ON	2005/02/28 14:12
L16	759	438/591	USPAT	OR	ON	2005/02/28 14:12
L17	440	438/775	USPAT	OR	ON	2005/02/28 14:12
L18	449	438/769	USPAT	OR	ON	2005/02/28 14:13
L19	835	438/770	USPAT	OR	ON	2005/02/28 14:13
L20	611	438/791	USPAT	OR	ON	2005/02/28 14:13